

Rejections Under 35 U.S.C. §102

In the Office Action, claims 1-8, 10-18 and 20-24 have been rejected under 35 U.S.C. §102(b) for being anticipated by U. S. Patent No. 5,247,289 issued to Matsueda, *et al.* ("Matsueda"). This rejection is respectfully traversed.

Independent claim 1 recites "[a] liquid crystal display, comprising: ... *a light interception pattern formed of the same material as the semiconductor pattern*". In this regard, the Examiner asserted that, in Fig. 7 of Matsueda, the portion of a amorphous silicon layer 78 overlying a common electrode 81 corresponds to the claimed light interception pattern. This assertion is respectfully disagreed with.

Matsueda neither teaches or suggests that the portion of the amorphous silicon layer 78 performs intercepting light. Also, the Office Action fails to point out which portion of Matsueda teaches or even remotely suggest that the portion of the amorphous silicon layer 78 performs any kind of light intercepting functions.

This is further evidenced by the fact that, in Fig. 7 of Matsueda, the portion of the amorphous silicon layer 78 is blocked by a common electrode 81 formed on a TFT substrate 71. As shown therein, the common electrode 81 extends beyond the periphery of the portion of the amorphous silicon layer 78. Furthermore, a light screen layer 85 is provided on a counter substrate 72 and extends beyond the periphery of the portion of the amorphous silicon layer 78. Thus, it is clear from Fig. 7 of Matsueda that the portion of the amorphous silicon layer 78 does not function as a light intercepting pattern.

It is respectfully submitted that Matsueda fails to teach or even remotely suggest the claimed feature of "a light interception pattern formed of the same material as the semiconductor

pattern". Thus, Applicant respectfully submits that independent claim 1 is patentable over Matsueda.

Independent claims 10 recites "a *light interception pattern* formed on the gate insulating layer and formed of the same material as said semiconductor pattern" and independent claim 22 recites "forming a semiconductor pattern and a *light interception pattern*, both formed of the same material, on the gate insulating layer". Thus, independent claims 10 and 22 would be also patentable over Matsueda.

Accordingly, Applicants respectfully request that the rejection over independent claims 1, 10 and 22 and their dependent claims 2-8, 11-18, 20, 21, 23 and 24 be withdrawn.

Rejections Under 35 U.S.C. §103

In the Office Action, claims 9 and 19 have been rejected under 35 U.S.C. §103(a) for being unpatentable over Matsueda in view of U. S. Patent No. 6,377,323 issued to Ono, *et al.* ("Ono"). This rejection is respectfully traversed.

Claims 9 and 19 are dependent from independent claims 1 and 10. As previously mentioned, Matsueda fails to teach the claimed feature of the light interception pattern that is formed of the same material as the semiconductor pattern of the thin film transistor.

In this regard, Ono teaches, in Figs. 1 and 2, a light blocking film SKD overlapped by data lines DL. However, the light block film SKD is formed below a gate insulator GI and a semiconductor layer AS is formed on the gate insulator GI. There is no explicit teaching or implicit suggestion from Ono that the light block film SKD is formed of the same material as a semiconductor layer AS in Fig. 3.

As discussed above, none of the applied reference teaches or suggests the claimed light interception pattern that is formed of the same material as the semiconductor pattern of the thin film transistor. Thus, it would not have been obvious to combine the teachings of the applied references to arrive at the invention defined in claim 1 and 10.

Accordingly, Applicants respectfully request that the rejection over claims 9 and 19 be withdrawn.

Other Matters

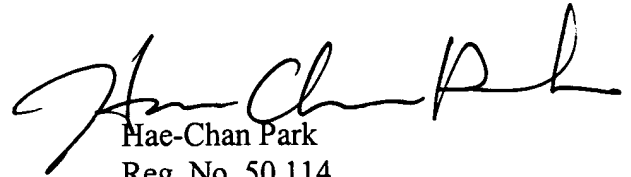
In this response, claims 1-34 have been amended for solely clarification purposes. Also, claims 35-38 are newly added.

CONCLUSION

All of the stated grounds of objection and rejection have been properly traversed, accommodated, or rendered moot. Applicant therefore respectfully requests that the Examiner reconsider all presently outstanding objections and rejections and that they be withdrawn. Applicant believes that a full and complete response has been made to the outstanding Office Action and, as such, claims 1-38 are in condition for allowance. If the Examiner believes, for any reason, that personal communication will expedite prosecution of this application, the Examiner is invited to telephone the undersigned at the number provided.

Prompt and favorable consideration of this Amendment is respectfully requested.

Respectfully submitted,



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